DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Apr 22 1999 Apr 23



FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

• Industrial high gain amplification.

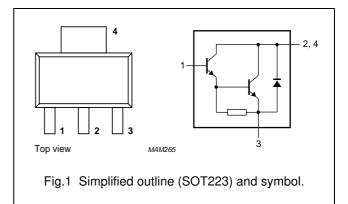
DESCRIPTION

NPN Darlington transistor in a SOT223 plastic package. PNP complements: BSP60, BSP61 and BSP62.

BSP50; BSP51; BSP52

PINNING

PIN	DESCRIPTION	
1	base	
2,4	collector	
3	emitter	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage o	pen emitter			
	BSP50		-	60	V
	BSP51		-	80	V
	BSP52		_	90	V
V _{CES}	collector-emitter voltage V	/ _{BE} = 0			
	BSP50		_	45	V
	BSP51		-	60	V
	BSP52		_	80	V
V _{EBO}	emitter-base voltage o	pen collector	_	5	V
l _C	collector current (DC)		_	1	А
I _{CM}	peak collector current		_	2	А
IB	base current (DC)		_	100	mA
P _{tot}	total power dissipation T	amb ≤ 25 °C; note 1	_	1.25	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for the SOT223 in the General Part of associated Handbook"*.

BSP50; BSP51; BSP52

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	note 1	96	K/W	
R _{th j-s}	thermal resistance from junction to solder point		17	K/W	

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for the SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

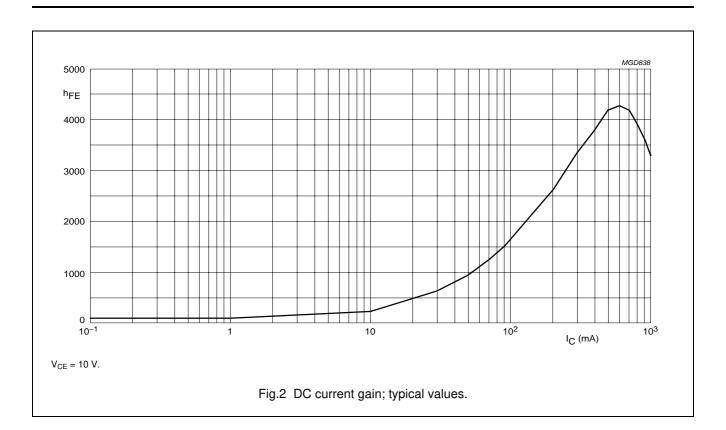
 $T_i = 25 \ ^\circ C$ unless otherwise specified.

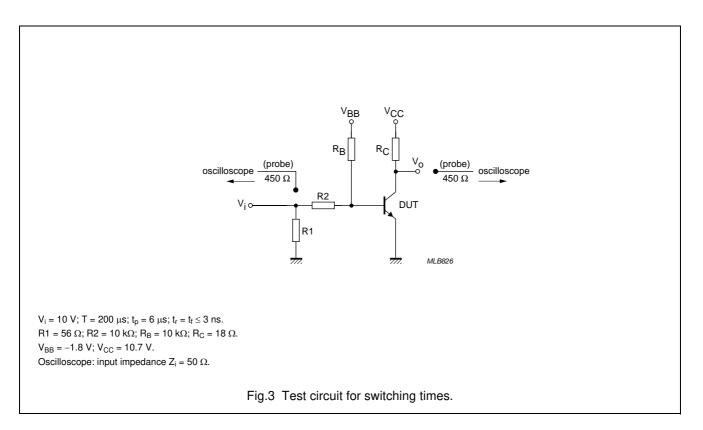
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES}	collector cut-off current					
	BSP50	$V_{BE} = 0; V_{CE} = 45 V$	_	_	50	nA
	BSP51	$V_{BE} = 0; V_{CE} = 60 V$	_	_	50	nA
	BSP52	$V_{BE} = 0; V_{CE} = 80 V$	_	-	50	nA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = 4 V$	_	_	50	nA
h _{FE}	DC current gain	V _{CE} = 10 V; note 1; see Fig.2				
		I _C = 150 mA	1000	-	-	
		I _C = 500 mA	2000	_	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 500 \text{ mA}; I_{B} = 0.5 \text{ mA}$	_	-	1.3	V
		$I_{C} = 500 \text{ mA}; I_{B} = 0.5 \text{ mA};$ $T_{j} = 150 \text{ °C}$	-	-	1.3	V
V _{BEsat}	base-emitter saturation voltage	I _C = 500 mA; I _B = 0.5 mA	-	-	1.9	V
f _T	transition frequency	$I_{C} = 500 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	_	200	_	MHz
Switching t	Switching times (between 10% and 90% levels); see Fig.3					
t _{on}	turn-on time	I _{Con} = 500 mA; I _{Bon} = 0.5 mA;	-	500	_	ns
t _{off}	turn-off time	$I_{Boff} = -0.5 \text{ mA}$	_	1300	-	ns

Note

1. Pulse test: $t_p \leq 300 \ \mu s; \ \delta \leq 0.02.$

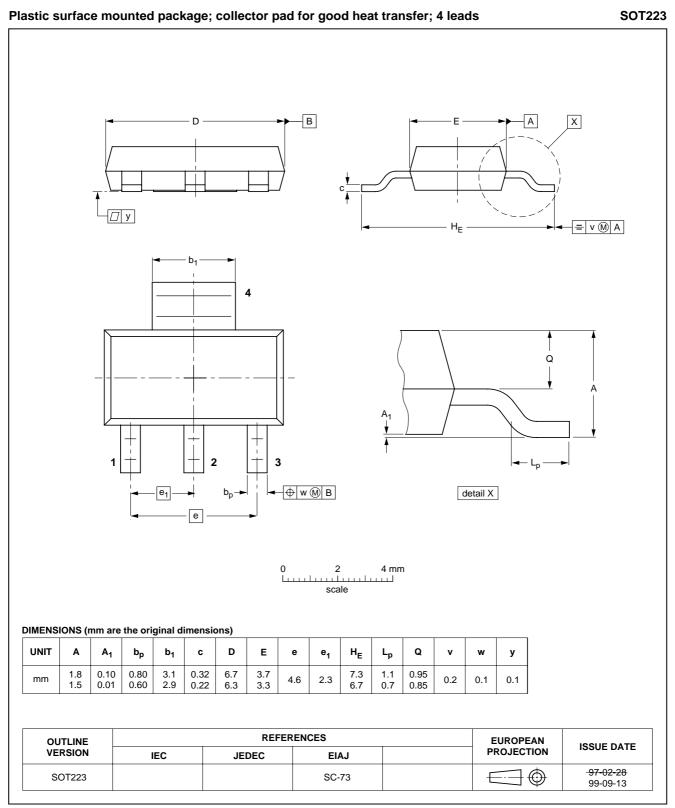
BSP50; BSP51; BSP52





BSP50; BSP51; BSP52

PACKAGE OUTLINE



BSP50; BSP51; BSP52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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Printed in The Netherlands

115002/00/03/pp7

Date of release: 1999 Apr 23

Document order number: 9397 750 05809

